

Amendment to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. – 12. (canceled)

13. (currently amended) A method comprising:

depositing a first metallic film on a substrate, the first metallic film containing two or more specific metals;

depositing a second metallic film on the substrate;

depositing a layer of photoresist on the first metallic film;

patterning the photoresist such that a desired portion of the first metallic film is masked and an undesired portion of the first metallic film is exposed;

selecting two or more chelating agents based upon the two or more specific metals contained in the first metallic film; and

using the two or more chelating agents to remove the undesired portion of the first metallic film, wherein the two or more chelating agents do not impair the a second metallic film ~~that does not contain the two or more specific metals contained in the metallic film.~~

14. (currently amended) The method of claim ~~12~~ 13 further comprising:
- selecting a media in which to employ the two or more chelating agents based upon
- the two or more specific metals contained in the first metallic film.
15. (canceled)
16. (previously presented) The method of claim 13 wherein the two or more chelating agents are employed in a solution at a concentration ranging from approximately 0.5 – 5 moles/liter, for each chelating agent.
17. (previously presented) The method of claim 14 wherein the two or more chelating agents are employed in a solution selected from the group consisting of an acidic solution, a basic solution, a solvent solution, and a de-ionized water solution.
18. (currently amended) A method comprising:
- depositing a first metallic film on a substrate, the first metallic film containing two or more specific metals;
- depositing a second metallic film on the substrate;
- depositing a layer of photoresist on the first metallic film;
- patterning the photoresist such that a desired portion of the first metallic film is masked and an undesired portion of the first metallic film is exposed;

selecting a media in which to employ two or more chelating agents based upon the two or more specific metals contained in the first metallic film; and employing the two or more chelating agents to remove the undesired portion of the first metallic film, wherein the two or more chelating agents do not impair the a second metallic film ~~that does not contain the two or more specific metals contained in the metallic film.~~

19. (currently amended) The method of claim 18 further comprising:

selecting the two or more chelating agents based upon the two or more specific metals contained in the first metallic film.

20. (original) The method of claim 19 wherein the media is a liquid media selected from the group consisting of an aqueous acid media with oxidant, an aqueous acid media without oxidant, an aqueous basic media without oxidant, and a solvent media without oxidant having a pH of approximately seven.

21. (previously presented) The method of claim 18 wherein the two or more chelating agents are employed in a solution at a concentration ranging from approximately 0.5 – 5 moles/liter, for each chelating agent.

22. (currently amended) The method of claim 13 wherein the two or more chelating agents are used in proportion to the proportion of the respective two or more specific metals of the first metallic film.

23. (currently amended) The method of claim 13 wherein the two or more chelating agents are specifically tailored to bind with the two or more specific metals in the first metallic film.

24. (currently amended) The method of claim 18 wherein the two or more chelating agents are used in proportion to the proportion of the respective two or more specific metals of the first metallic film.

25. (currently amended) The method of claim 18 wherein the two or more chelating agents are specifically tailored to bind with the two or more specific metals in the first metallic film.

26. (previously presented) A method for making a semiconductor structure comprising:
depositing a first metal-containing film above a substrate, wherein said metal-containing film comprises one or more metals;
depositing a second metal-containing film above said first metal-containing film,
wherein said second metal-containing film comprises two or more metals;
depositing a masking layer above said second metal-containing film;

patterning said masking layer such that a desired portion of said second metal-containing film is masked and an undesired portion of said second metal-containing film is exposed; and
removing said undesired portion of said second metal-containing film with a solution comprising two or more chelating agents, wherein said solution does not impair said first metal-containing film.

27. (previously presented) The method of claim 26 wherein the two or more chelating agents are specifically tailored to bind with the two or more metals in said first metal-containing film.

28. (previously presented) The method of claim 26 wherein the two or more chelating agents are used in proportion to the proportion of the respective two or more metals of said first metal-containing film.

29. (previously presented) The method of claim 26 wherein said first metal-containing film does not comprise the two or more metals in said second metal-containing film.

30. (previously presented) The method of claim 29 wherein the two or more chelating agents are specifically tailored to bind with the two or more metals in said first metal-containing film.

31. (previously presented) The method of claim 29 wherein the two or more chelating agents are used in proportion to the proportion of the respective two or more metals of said first metal-containing film.